TOSHIBA Photocoupler IRED & Photo-Transistor

TLP731, TLP732

Office Machine
Household Use Equipment
Solid State Relay
Switching Power Supply

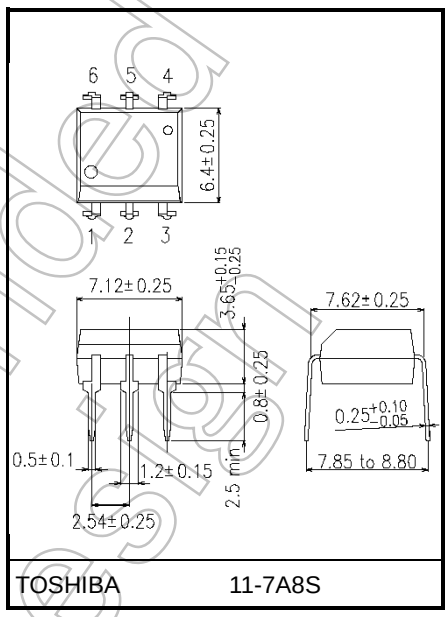
The TOSHIBA TLP731 and TLP732 consist of a photo-transistor optically coupled to a gallium arsenide infrared emitting diode in a six lead plastic DIP package.
TLP732 is no-base internal connection for high-EMI environments.

- Collector-emitter voltage: 55V (min)
- Current transfer ratio: 50% (min)
  Rank GB: 100% (min)
- Isolation voltage: 4000 V_{rms} (min)
- UL-recognized: UL 1577, File No.E67349
- cUL-recognized: CSA Component Acceptance Service No.5A
  File No.E67349
- VDE-approved: EN 60747-5-5 (Note 1)

Note 1 : When a VDE approved type is needed,
please designate the **Option (D4)**.

- Creepage distance : 7.0mm (min)
  Clearance : 7.0 mm (min)
  Insulation thickness : 0.5 mm (min)

Unit: mm

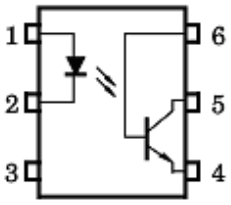


TOSHIBA 11-7A8S

Weight: 0.35 g (typ.)

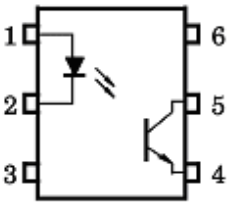
Pin Configurations (top view)

TLP731



1 : ANODE
2 : CATHODE
3 : NC
4 : EMITTER
5 : COLLECTOR
6 : BASE

TLP732



1 : ANODE
2 : CATHODE
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6 : NC

Start of commercial production
1985-02

Not Recommended for New Design

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Current Transfer Ratio

Classification (Note 1)	Current Transfer Ratio (%) (I_C / I_F) I_F = 5 mA, V_{CE} = 5 V, Ta = 25°C		Marking Of Classification
	Min	Max	
Blank	50	600	Blank, Y■, YE, G, G■, GR, B, BL, GB
Rank Y	50	150	YE, Y■
Rank GR	100	300	GR, G, G■
Rank BL	200	600	BL, B
Rank GB	100	600	GB, GR, G, G■, BL, B,

Note: The product with the Rank Y and BL are limited in production.
For details, please contact your nearest Toshiba sales representative.

Note 1: Ex. rank GB: TLP731 (GB)

Note: Application type name for certification test,
please use standard product type name, i.e.
TLP731(GB): TLP731
TLP732(GB): TLP732

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Absolute Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating	Unit
LED	Forward current	I_F	60	mA
	Forward current derating (Ta ≥ 39°C)	ΔI_F / °C	-0.7	mA / °C
	Peak forward current (100μs pulse, 100pps)	I_{FP}	1	A
	Power dissipation	P_D	70	mW
	Power dissipation derating (Ta ≥ 39°C)	ΔP_D / °C	-0.82	mW / °C
	Reverse voltage	V_R	5	V
	Junction temperature	T_j	125	°C
Detector	Collector-emitter voltage	V_{CEO}	55	V
	Collector-base voltage (TLP731)	V_{CBO}	80	V
	Emitter-collector voltage	V_{ECO}	7	V
	Emitter-base voltage (TLP731)	V_{EBO}	7	V
	Collector current	I_C	50	mA
	Power dissipation	P_C	150	mW
	Power dissipation derating (Ta ≥ 25°C)	ΔP_C / °C	-1.5	mW / °C
	Junction temperature	T_j	125	°C
Storage temperature range		T_{stg}	-55 to 125	°C
Operating temperature range		T_{opr}	-55 to 100	°C
Lead soldering temperature (10 s)		T_{sol}	260	°C
Total package power dissipation		P_T	250	mW
Total package power dissipation derating (Ta ≥ 25°C)		ΔP_T / °C	-2.5	mW / °C
Isolation voltage (AC, 60 s, R.H. ≤ 60 %) (Note 1)		BV_S	4000	Vrms

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook (“Handling Precautions”/“Derating Concept and Methods”) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Device considered a two terminal device: LED side pins shorted together and detector side pins shorted together.

Recommended Operating Conditions

Characteristic	Symbol	Min	Typ.	Max	Unit
Supply voltage	V_{CC}	—	5	24	V
Forward current	I_F	—	16	25	mA
Collector current	I_C	—	1	10	mA
Operating temperature	T_{opr}	-25	—	85	°C

Note: Recommended operating conditions are given as a design guideline to obtain expected performance of the device. Additionally, each item is an independent guideline respectively. In developing designs using this product, please confirm specified characteristics shown in this document.

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Electrical Characteristics (Ta = 25°C)

Characteristic			Symbol	Test Condition	Min	Typ.	Max	Unit
LED	Forward voltage		V_F	I_F = 10 mA	1.0	1.15	1.3	V
	Reverse current		I_R	V_R = 5 V	—	—	10	μA
	Capacitance		C_T	V = 0 V, f = 1 MHz	—	30	—	pF
Detector	Collector-emitter breakdown voltage		$V_{(BR)CEO}$	I_C = 0.5 mA	55	—	—	V
	Emitter-collector breakdown voltage		$V_{(BR)ECO}$	I_E = 0.1mA	7	—	—	V
	Collector-base breakdown voltage	(TLP731)	$V_{(BR)CBO}$	I_C = 0.1mA	80	—	—	V
	Emitter-base breakdown voltage	(TLP731)	$V_{(BR)EBO}$	I_E = 0.1mA	7	—	—	V
	Collector dark current		I_{CEO}	V_{CE} = 24 V	—	10	100	nA
				V_{CE} = 24 V, Ta = 85 °C	—	2	50	μA
	Collector dark current	(TLP731)	I_{CER}	V_{CE} = 24 V, Ta = 85 °C R_{BE} = 1 MΩ	—	0.5	10	μA
	Collector dark current	(TLP731)	I_{CBO}	V_{CB} = 10 V	—	0.1	—	nA
	DC forward current gain	(TLP731)	h_{FE}	V_{CE} = 5 V, I_C = 0.5 mA	—	400	—	—
	Capacitance collector to emitter		C_{CE}	V = 0 V, f = 1 MHz	—	10	—	pF

Coupled Electrical Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Condition		Min	Typ.	Max	Unit
Current transfer ratio		I_C / I_F	I_F = 5 mA, V_{CE} = 5 V		50	—	600	%
				Rank GB	100	—	600	
Saturated CTR		I_C / $I_{F\ (sat)}$	I_F = 1 mA, V_{CE} = 0.4 V		—	60	—	%
				Rank GB	30	—	—	
Base photo-current	(TLP731)	I_{PB}	I_F = 5 mA, V_{CB} = 5 V		—	10	—	μA
Collector-emitter saturation voltage		$V_{CE\ (sat)}$	I_C = 2.4 mA, I_F = 8 mA		—	—	0.4	V
			I_C = 0.2 mA, I_F = 1 mA		—	0.2	—	
				Rank GB	—	—	0.4	

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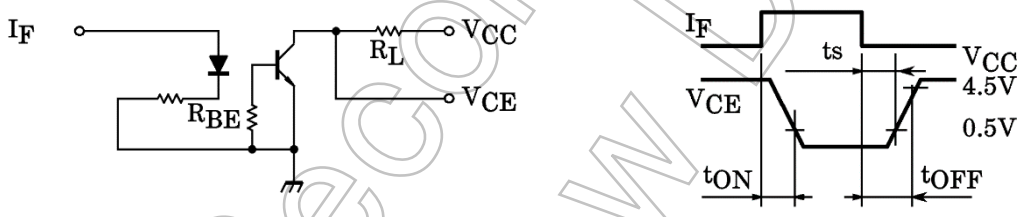
Isolation Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min	Typ.	Max	Unit
Capacitance (input to output)	C_S	V_S = 0 V, f = 1 MHz	—	0.8	—	pF
Isolation resistance	R_S	V_S = 500 V, R.H.≤60 %	1×10^{12}	10^{14}	—	Ω
Isolation voltage	BV_S	AC, 60 s	4000	—	—	Vrms

Switching Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min	Typ.	Max	Unit
Rise time	t_r	V_{CC} = 10 V, I_C = 2 mA R_L = 100 Ω	—	2	—	μs
Fall time	t_f		—	3	—	
Turn-on time	t_{on}		—	3	10	
Turn-off time	t_{off}		—	3	10	
Turn-on time	t_{ON}	R_L = 1.9 kΩ (Fig.1) R_{BE} = open V_{CC} = 5 V, I_F = 16 mA	—	2	—	μs
Storage time	t_s		—	15	—	
Turn-off time	t_{OFF}		—	25	—	
Turn-on time	t_{ON}	R_L = 1.9 kΩ (Fig.1) R_{BE} = 220 kΩ (TLP731) V_{CC} = 5 V, I_F = 16 mA	—	2	—	μs
Storage time	t_s		—	12	—	
Turn-off time	t_{OFF}		—	20	—	

Fig. 1 Switching time test circuit



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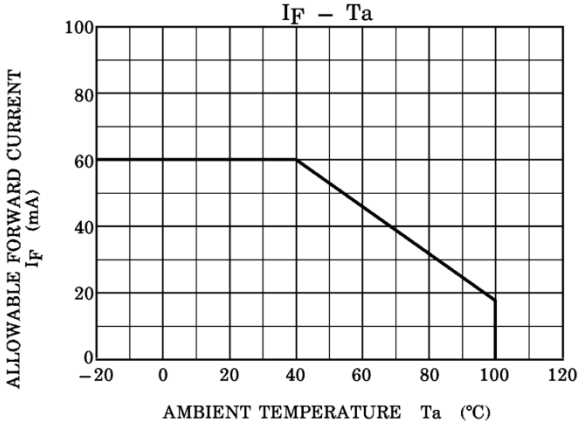
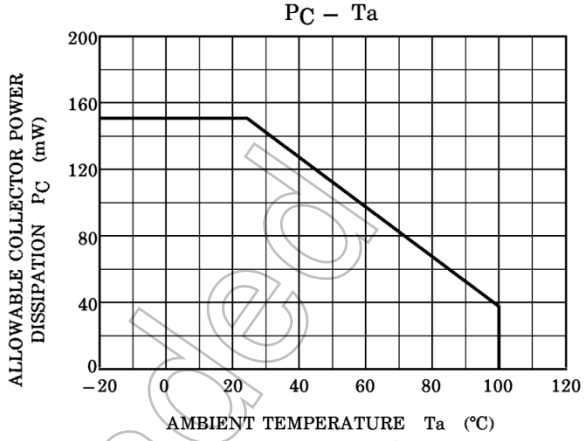
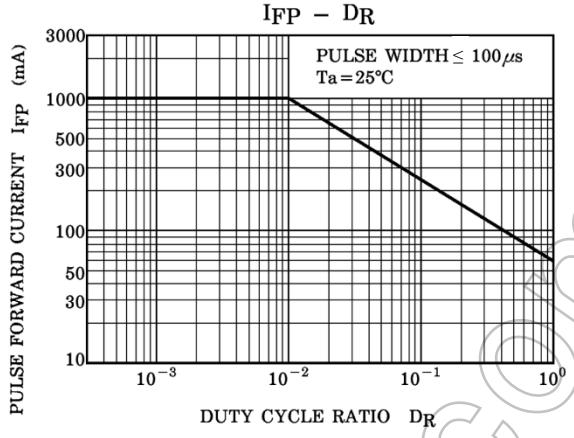
I_F – Ta



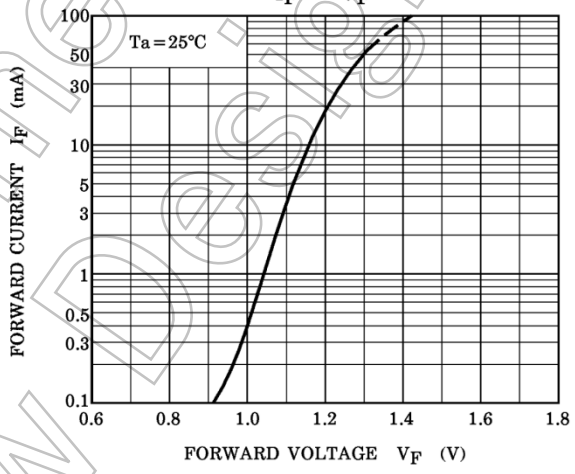
P_C – Ta



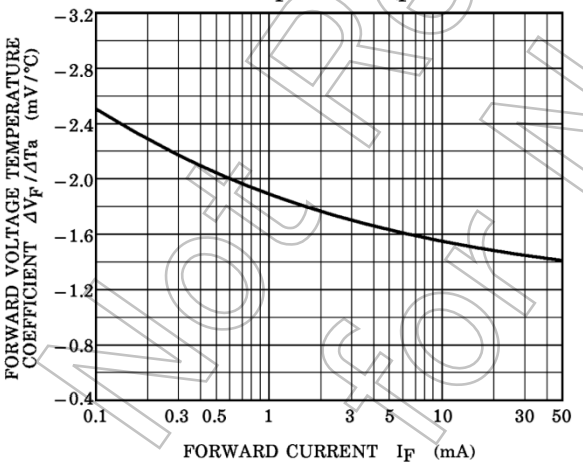
I_{FP} – D_R



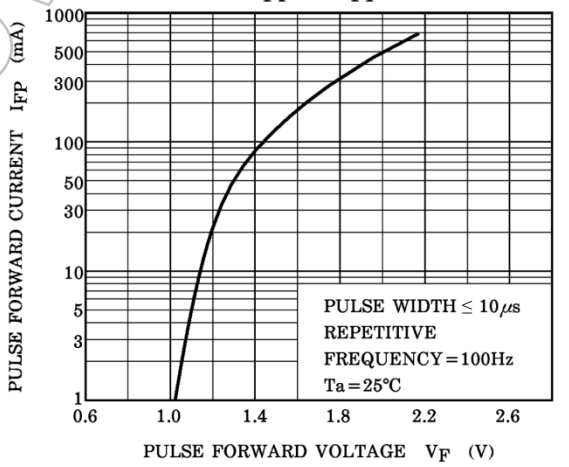
I_F – V_F



$\Delta V_F / \Delta Ta$ – I_F



I_{FP} – V_{FP}



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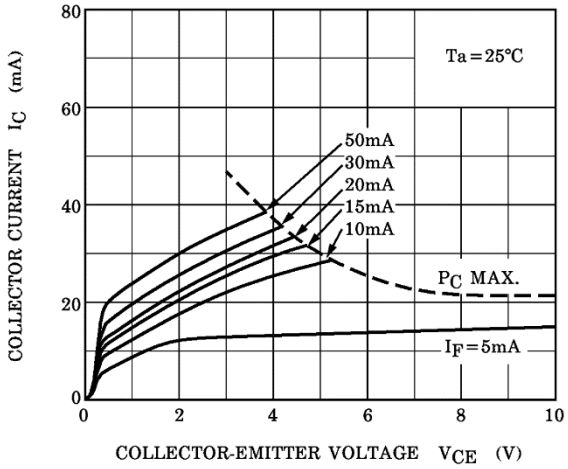
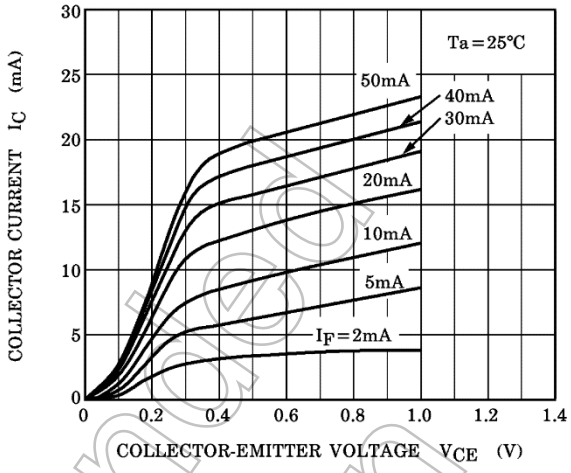
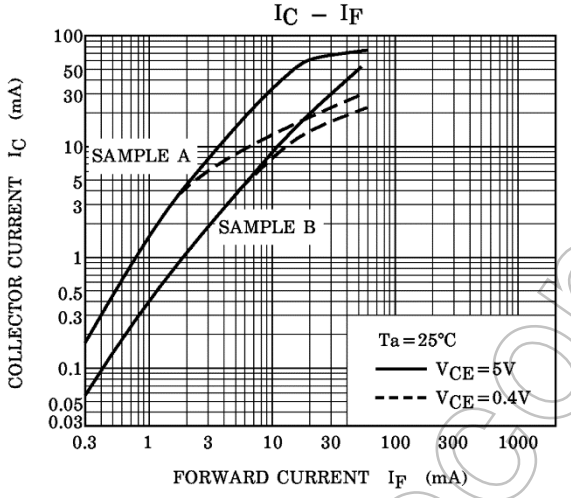
$I_C - V_{CE}$



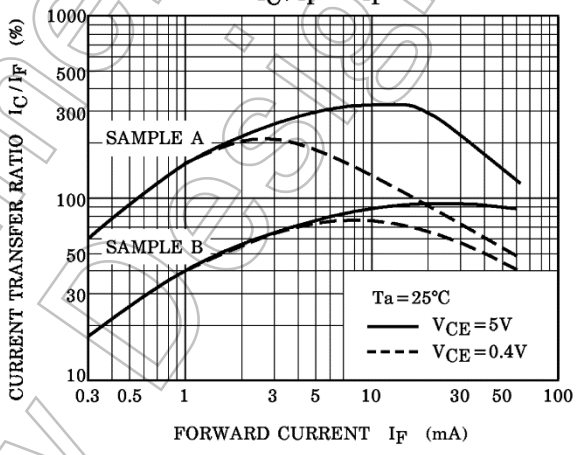
$I_C - V_{CE}$



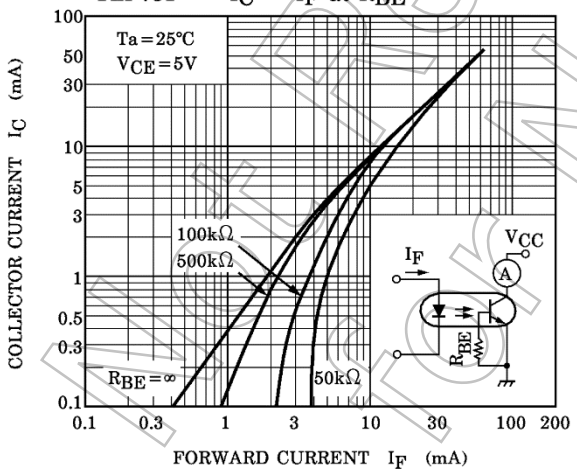
$I_C - I_F$



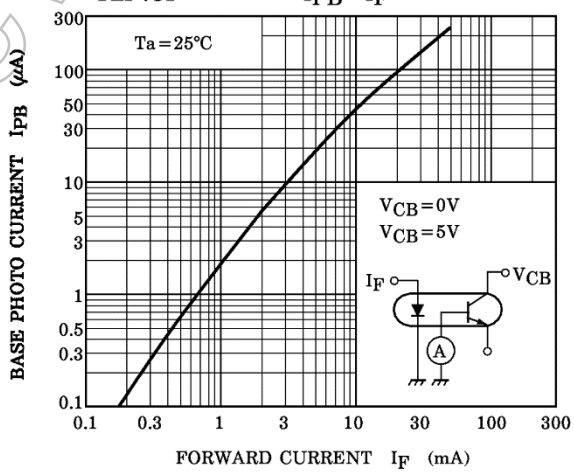
$I_C / I_F - I_F$



TLP731 $I_C - I_F$ at R_{BE}



TLP731 $I_{PB} - I_F$



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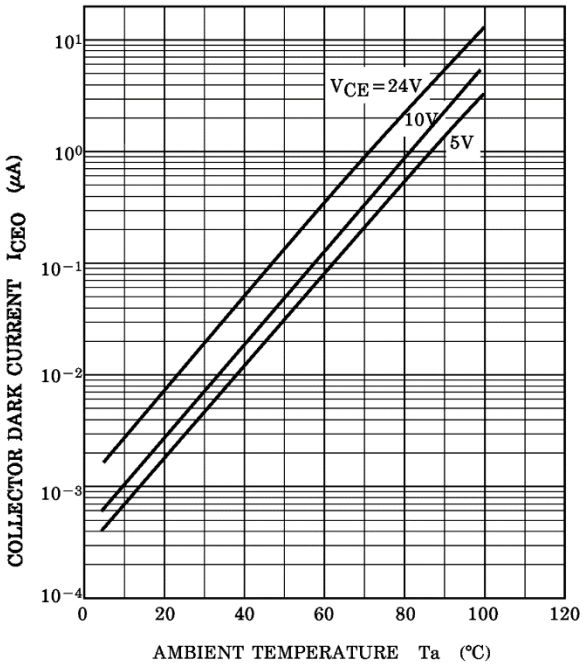
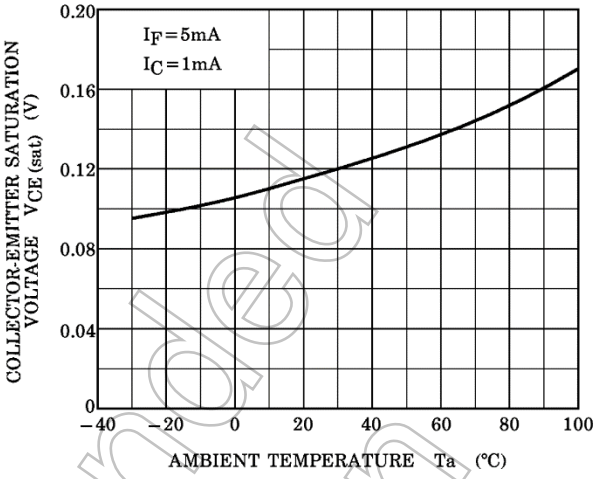
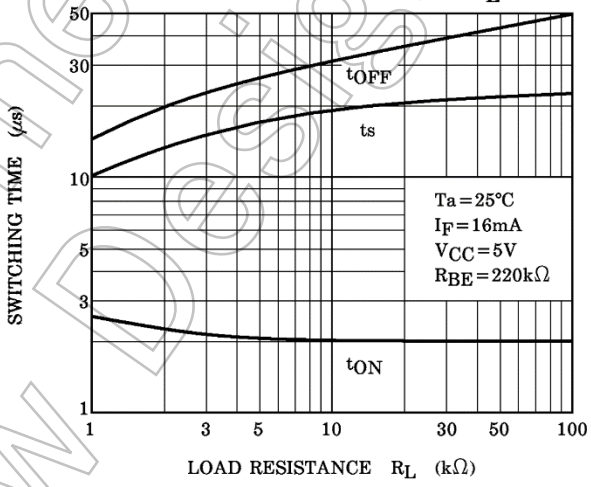
I_{CEO} – Ta



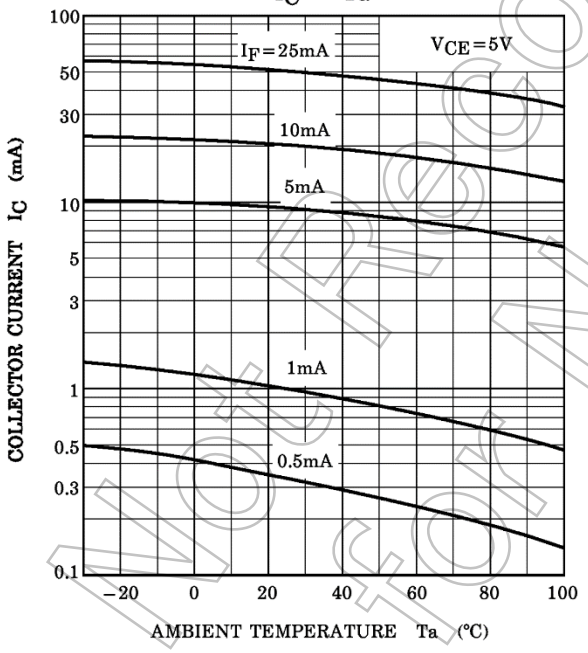
$V_{CE\,(sat)}$ – Ta



TLP731 SWITCHING TIME – R_L



I_C – Ta



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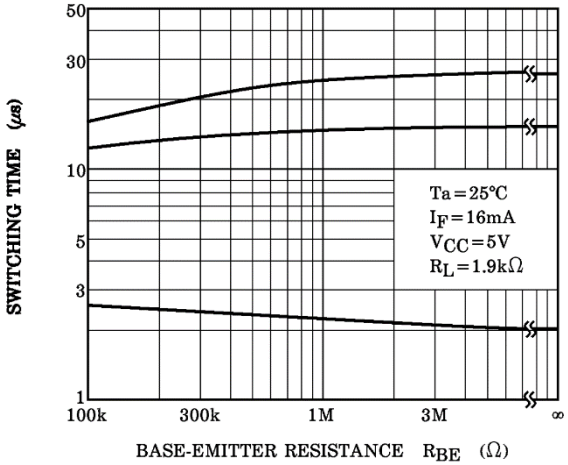
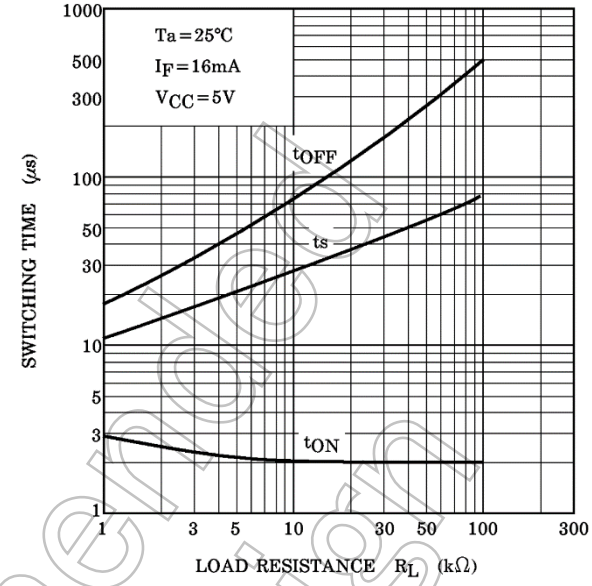
TLP731 SWITCHING TIME – R_{BE}



SWITCHING TIME – R_L



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